

SILICON SCHOTTKY RECTIFIER
Ultra Low Reverse Leakage
175°C Operating Temperature

Applications:

- Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	Maximum DC Output Current (@ $T_C=100^\circ\text{C}$) (Single, Doubler)	7.5	A
Max. Average Forward Current	$I_{F(AV)}$	Maximum DC Output Current (@ $T_C=100^\circ\text{C}$) (Common Cathode, Common Anode)	15	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave	75	A
Maximun Thermal Resistance (Single)	$R_{\theta JC}$	-	2.71	$^\circ\text{C/W}$
Maximun Thermal Resistance (Common Cathode, Common Anode, Doubler)	$R_{\theta JC}$	-	1.36	$^\circ\text{C/W}$
Max. Junction Temperature	T_J	-	-65 to +175	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$

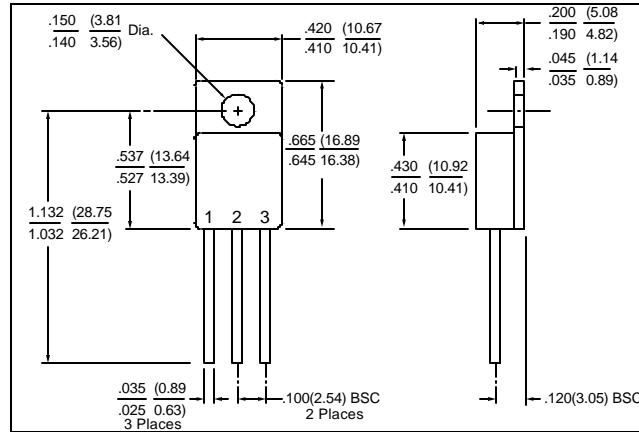
Electrical Characteristics Per Leg:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 7.5 A, Pulse, $T_J = 25^\circ\text{C}$	0.73	V
	V_{F2}	@ 7.5 A, Pulse, $T_J = 125^\circ\text{C}$	0.66	V
Max. Reverse Current	I_{R1}	@ $V_R = 45\text{ V}$, Pulse, $T_J = 25^\circ\text{C}$	0.2	mA
	I_{R2}	@ $V_R = 45\text{ V}$, Pulse, $T_J = 125^\circ\text{C}$	7.5	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$, $V_{SIG} = 50\text{ mV (p-p)}$	400	pF

SENSITRON

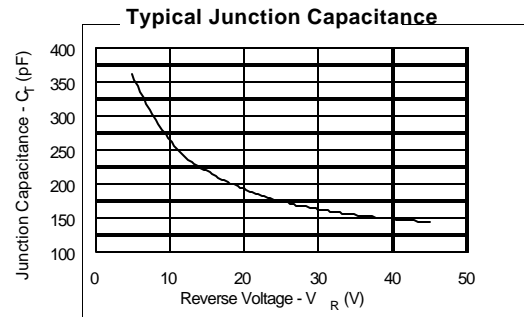
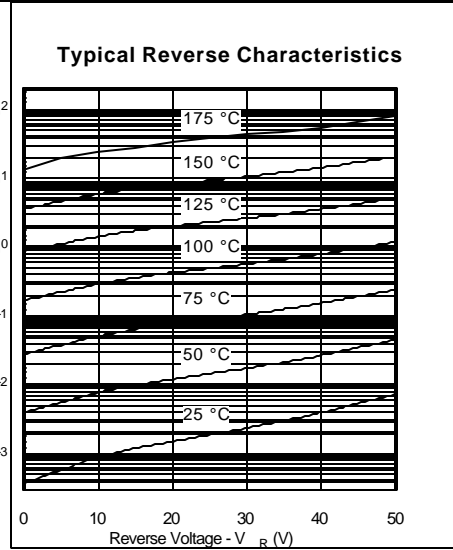
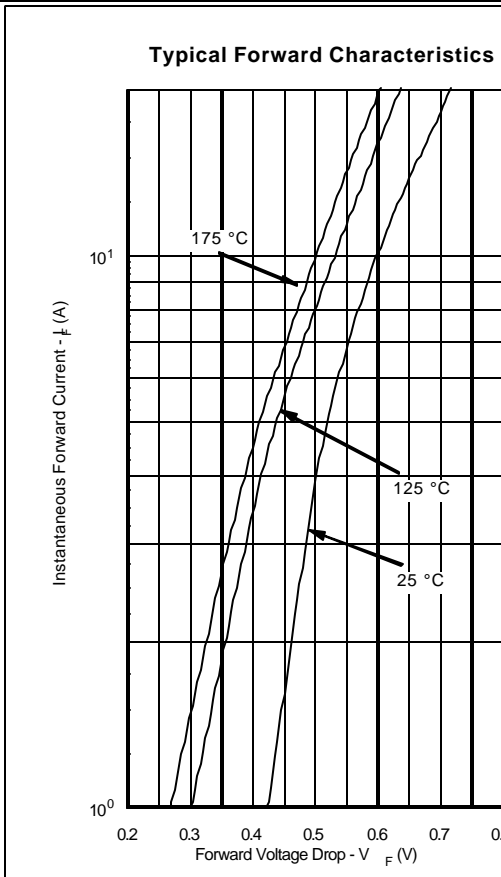
**TECHNICAL DATA
 DATASHEET 4753, REV. A**

Mechanical Dimensions: In Inches / mm



TO-257

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DOUBLER (D)	ANODE	CATHODE / ANODE	CATHODE



Note: V_f characteristics are for unpackaged die only.

TECHNICAL DATA

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